PROGRAMMABLE OVERVOLTAGE PROTECTOR
QUAD FORWARD-CONDUCTING P-GATE THYRISTOR

TISP61089Q SLIC Overvoltage Protector

Quad Voltage-Programmable Protector
- Wide -20 V to -155 V Programming Range
- Low 5 mA max. Gate Triggering Current
- High 150 mA min. Holding Current

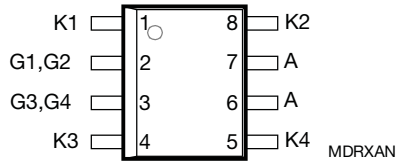
10/700 Protection Voltage Specified

Element	Protection Level 40 A, 10/700
Diode	+12
Crowbar V_{GG} = -48 V	-64

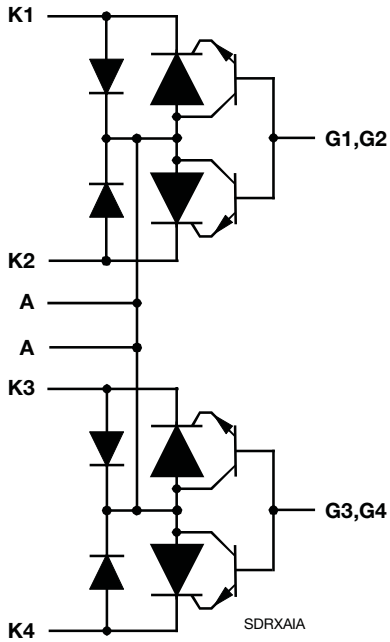
Rated for ITU-T and YD/T-950 10/700 impulses

Also rated for Telcordia Intra-building impulses

D Package (Top View)



Device Symbol



Description

The TISP61089Q is a quad forward-conducting buffered p-gate overvoltage protector. It is designed to protect monolithic SLICs (Subscriber Line Interface Circuits) against overvoltages on the telephone line caused by lightning, a.c. power contact and induction. The TISP61089Q limits voltages that exceed the SLIC supply rail voltage. The TISP61089Q parameters are specified to allow equipment compliance with Bellcore GR-1089-CORE, ITU-T K.20, K.21 and K.45 and YD/T-950.

The SLIC line driver section is typically powered from 0 V (ground) and a negative voltage in the region of -20 V to -75 V. The protector gate is connected to this negative supply. This references the protection (clipping) voltage to the negative supply voltage. As the protection voltage will then track the negative supply voltage the overvoltage stress on the SLIC is minimized.

Positive overvoltages are clipped to ground by diode forward conduction. Negative overvoltages are initially clipped close to the SLIC negative supply rail value. If sufficient current is available from the overvoltage, then the protector will crowbar into a low voltage on-state condition. As the overvoltage subsides, the high holding current of the crowbar prevents d.c. latchup.

The TISP61089Q is intended to be used with a series combination of a 25 Ω or higher resistance and a suitable overcurrent protector. Power fault compliance requires the series overcurrent element to open-circuit or become high impedance (see Applications Information). For equipment compliant to ITU-T recommendations K.20 or K.21 only, the recommended 10 Ω series resistor value is set by the power cross requirements.

These monolithic protection devices are fabricated in ion-implanted planar vertical power structures for high reliability and are virtually transparent in normal operation. The TISP61089Q buffered gate design reduces the loading on the SLIC supply during overvoltages caused by power cross and induction. The TISP61089Q is available in an 8-pin plastic small-outline surface mount package.

How to Order

Device	Package	Carrier	Order As	Marking Code	Standard Quantity
TISP61089Q	8 Pin Small Outline (D008)	Embossed Tape Reeled	TISP61089QDR-S	1089Q	2500

*RoHS Directive 2002/95/EC Jan 27 2003 including Annex

JULY 2010

Specifications are subject to change without notice.
Customers should verify actual device performance in their specific applications.

Absolute Maximum Ratings, T_J = 25 °C (Unless Otherwise Noted)

Rating		Symbol	Value	Unit
Repetitive peak off-state voltage, I_G = 0	-40 °C ≤ T_J ≤ 85 °C	V_{DRM}	-170	V
Repetitive peak gate-cathode voltage, V_{KA} = 0	-40 °C ≤ T_J ≤ 85 °C	V_{GKRM}	-167	
Non-repetitive peak on-state pulse current (see Notes 1 and 2) 10/1000 µs (Bellcore GR-1089-CORE, Issue 1, November 1994, Section 4) 5/320 (ITU-T K.20/21/45, YD/T-950, open circuit voltage waveshape 10/700) 2/10 (Bellcore GR-1089-CORE, Issue 1, November 1994, Section 4)		I_{TSP}	 30 40 120	A
Non-repetitive peak on-state current, 60 Hz (see Notes 1, 2 and 3) 900 s		I_{TSM}	 0.5	A
Non-repetitive peak gate current, 2/10 µs pulse, cathodes commoned (see Notes 1 and 2)		I_{GSM}	40	A
Junction temperature		T_J	-40 to +150	°C
Storage temperature range		T_{stg}	-40 to +150	°C

NOTES: 1. Initially the protector must be in thermal equilibrium with T_J = 25 °C. The surge may be repeated after the device returns to its initial conditions.
2. These non-repetitive rated currents are peak values for either polarity. The rated current values may be applied to any cathode-anode terminal pair. Additionally, all cathode-anode terminal pairs may have their rated current values applied simultaneously (in this case the anode terminal current will be four times the rated current value of an individual terminal pair).
3. EIA/JESD51-2 environment and EIA/JESD51-7 high effective thermal conductivity test board (multi-layer) connected with 0.6 mm printed wiring track widths.

Recommended Operating Conditions

		Min	Typ	Max	Unit
C_G	Gate decoupling capacitor		100		nF
R_S	TISP61089Q series resistor for first-level and second-level surge survival TISP61089Q series resistor for first-level surge survival	40 25			Ω

Electrical Characteristics, T_J = 25 °C (Unless Otherwise Noted)

Parameter		Test Conditions		Min	Typ	Max	Unit
I_D	Off-state current	$V_D = V_{DRM}$, V_{GK} = 0				-5	µA
$V_{(BO)}$	Breakover voltage	10/700 µs, I_T = -40 A, R_S = 55 Ω, V_{GG} = -48 V, C_G = 100nF				-64	V
V_F	Forward voltage	I_F = 5 A, t_w = 200 µs				3	V
V_{FRM}	Peak forward recovery voltage	10/700 µs, I_F = 40 A, R_S = 55 Ω, V_{GG} = -48 V, C_G = 100nF			12		V
I_H	Holding current	I_T = -1 A, di/dt = 1 A/ms, V_{GG} = -100 V		-150			mA
I_{GAS}	Gate reverse current	$V_{GG} = V_{GK} = V_{GKRM}$, V_{KA} = 0				-5	µA
I_{GT}	Gate trigger current	I_T = 3 A, $t_{p(g)}$ ≥ 20 µs, V_{GG} = -100 V				5	mA
V_{GT}	Gate trigger voltage	I_T = 3 A, $t_{p(g)}$ ≥ 20 µs, V_{GG} = -100 V				2.5	V
C_{AK}	Anode-cathode off-state capacitance	f = 1 MHz, V_d = 1 V I_G = 0, (see Note 4)	V_D = -3V			100	pF
			V_D = -48V			50	

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Thermal Characteristics

Parameter		Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$	Junction to free air thermal resistance	P_{tot} = 0.8 W, T_A = 25 °C 5 cm^2, FR4 PCB			160	°C/W

Parameter Measurement Information

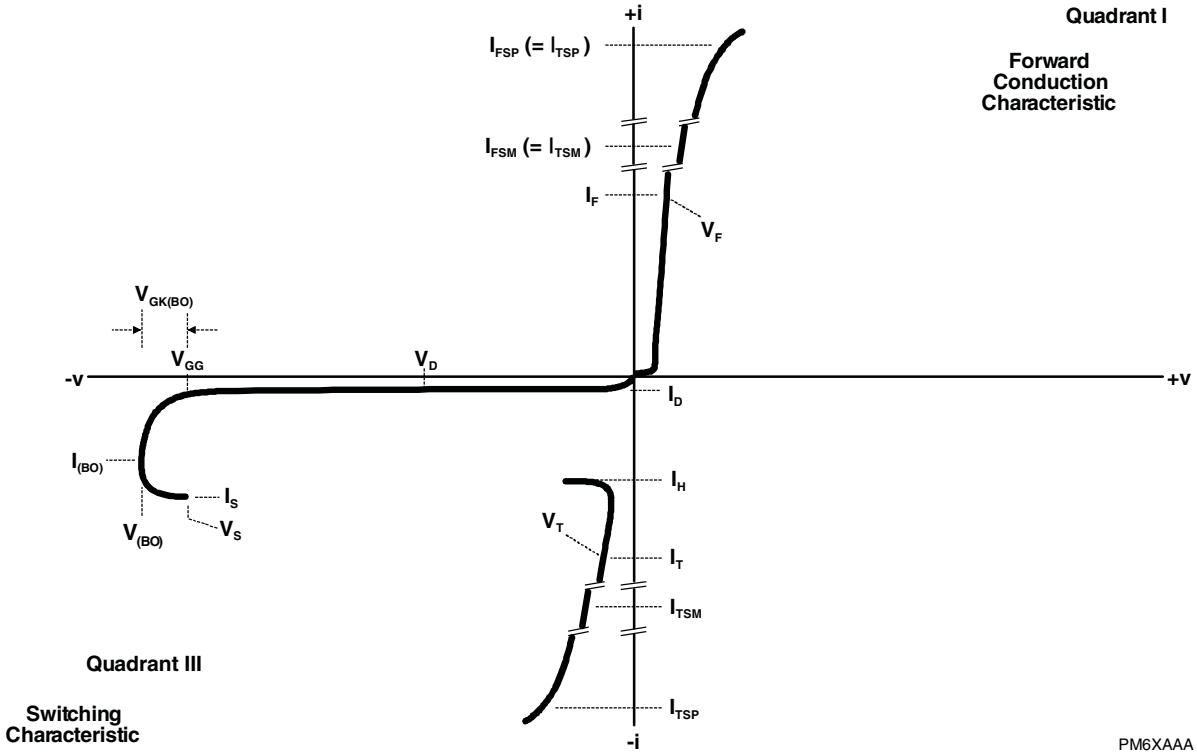

Figure 1. Voltage-Current Characteristic

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Applications Information

Typical Applications Circuit

Figure 2 shows a typical TISP61089Q SLIC card protection circuit. The incoming line conductors, Ring (R) and Tip (T), connect to the relay matrix via the series overcurrent protection. Positive temperature coefficient (PTC) resistors can be used for overcurrent protection. Resistors will reduce the prospective current from the surge generator for both the TISP61089Q and the ring/test protector.

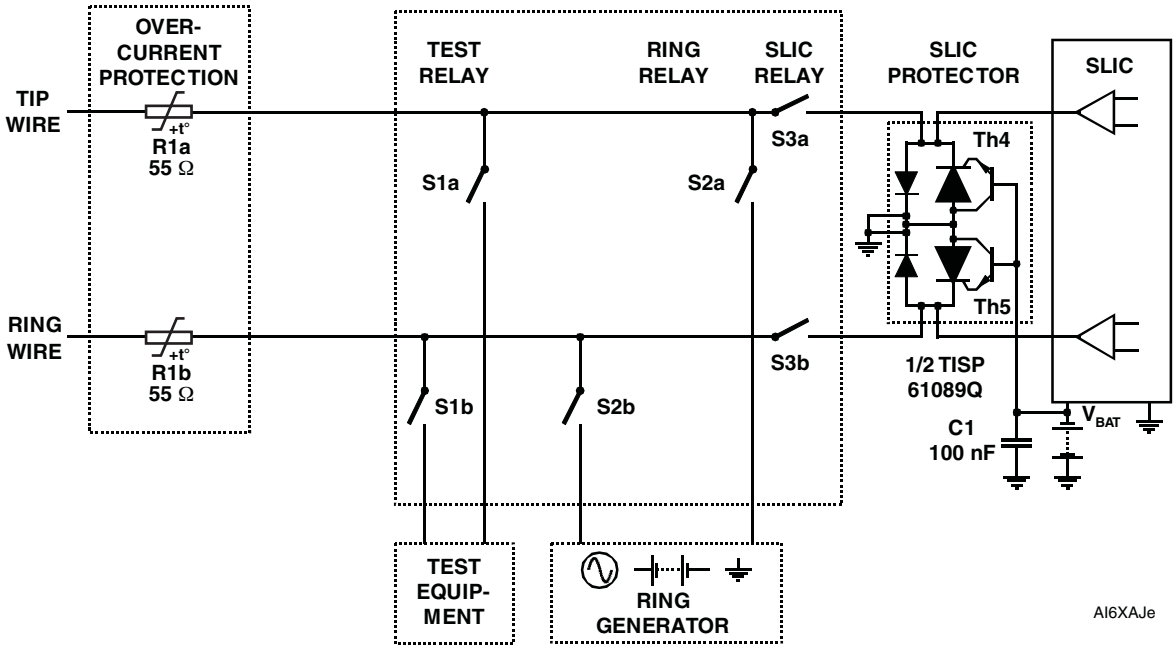

Figure 2. Typical Application Circuit

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